## MEMS Thermal Bimorph

## Important Details

- Beam length (determined by ACTV mask) $=620 \mu \mathrm{~m}$
- Beam width (determined by ACTV mask) $=80 \mu \mathrm{~m}$
- Width of ACTV-CONT lip $=8 \mu \mathrm{~m}$
- Resistor composed of three segments of varying linewidth:
- Segment A: $\mathrm{W}=24 \mu \mathrm{~m}, \mathrm{~L}=82 \mu \mathrm{~m}(\mathrm{~L}=62 \mu \mathrm{~m}$ from edge of second contact)
- Segment B: $\mathrm{W}=8 \mu \mathrm{~m}, \mathrm{~L}=120+8+104+8+104+8+120 \mu \mathrm{~m}$, Plus 6 corner squares
- Segment C: $\mathrm{W}=24 \mu \mathrm{~m}, \mathrm{~L}=82 \mu \mathrm{~m}$ ( $\mathrm{L}=62 \mu \mathrm{~m}$ from edge of second contact)


Masks: [- ACTV 脑 POLY $\square$ CONT $\mathbb{M}$ METL

